

# Qing Cai

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/4610042/publications.pdf>

Version: 2024-02-01

16  
papers

357  
citations

1307594

7  
h-index

940533

16  
g-index

17  
all docs

17  
docs citations

17  
times ranked

377  
citing authors

| #  | ARTICLE  | IF   | CITATIONS |
|----|--|------|-----------|
| 1  | Progress on AlGaIn-based solar-blind ultraviolet photodetectors and focal plane arrays. <i>Light: Science and Applications</i> , 2021, 10, 94.   | 16.6 | 193       |
| 2  | Performance of Monolayer Blue Phosphorene Double-Gate MOSFETs from the First Principles. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 20956-20964.  | 8.0  | 39        |
| 3  | Nanoplasmonically Enhanced High-Performance Metastable Phase $\hat{\mu}$ -Ga <sub>2</sub> O <sub>3</sub> Solar-Blind Photodetectors. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 40283-40289.  | 8.0  | 31        |
| 4  | Photoluminescence Study of the Photoinduced Phase Separation in Mixed-Halide Hybrid Perovskite CH <sub>3</sub> NH <sub>3</sub> Pb(BrxI <sup>1-x</sup> ) <sub>3</sub> Crystals Synthesized via a Solvothermal Method. <i>Scientific Reports</i> , 2017, 7, 17695. | 3.3  | 18        |
| 5  | $\hat{\mu}$ -Ga <sub>2</sub> O <sub>3</sub> : A Promising Candidate for High-Electron-Mobility Transistors. <i>IEEE Electron Device Letters</i> , 2020, , 1-1.   | 3.9  | 15        |
| 6  | An Improved Design for Solar-Blind AlGaIn Avalanche Photodiodes. <i>IEEE Photonics Journal</i> , 2017, 9, 1-7.   | 2.0  | 13        |
| 7  | Performance Modulation for Back-Illuminated AlGaIn Ultraviolet Avalanche Photodiodes Based on Multiplication Scaling. <i>IEEE Photonics Journal</i> , 2019, 11, 1-7.   | 2.0  | 10        |
| 8  | High-performance normally off p-GaN gate high-electron-mobility transistor with In <sub>0.17</sub> Al <sub>0.83</sub> N barrier layer design. <i>Optical and Quantum Electronics</i> , 2021, 53, 1.  | 3.3  | 7         |
| 9  | Back-illuminated AlGaIn heterostructure solar-blind avalanche photodiodes with one-dimensional photonic crystal filter. <i>Optics Express</i> , 2020, 28, 6027.  | 3.4  | 7         |
| 10 | Effects of the Trap Level in the Unintentionally Doped GaN Buffer Layer on Optimized p-GaN Gate AlGaIn/GaN HEMTs. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1700368.  | 1.8  | 5         |
| 11 | A High Quantum Efficiency Narrow-Band UV-B AlGaIn p-i-n Photodiode With Polarization Assistance. <i>IEEE Photonics Journal</i> , 2021, 13, 1-8.  | 2.0  | 5         |
| 12 | Self-Assembly Nanopillar/Superlattice Hierarchical Structure: Boosting AlGaIn Crystalline Quality and Achieving High-Performance Ultraviolet Avalanche Photodetector. <i>ACS Applied Materials &amp; Interfaces</i> , 2022, 14, 33525-33537.                     | 8.0  | 4         |
| 13 | A High-Performance SiO <sub>2</sub> /SiN <sub>x</sub> 1-D Photonic Crystal UV Filter Used for Solar-Blind Photodetectors. <i>IEEE Photonics Journal</i> , 2019, 11, 1-7.   | 2.0  | 3         |
| 14 | Direct observation of reach-through behavior in back-illuminated algan avalanche photodiode with separate absorption and multiplication structure. <i>Journal Physics D: Applied Physics</i> , 2020, 53, 425101.   | 2.8  | 3         |
| 15 | Low-Voltage p-i-n GaN-Based Alpha-Particle Detector With High Energy Resolution. <i>IEEE Electron Device Letters</i> , 2021, 42, 1755-1758.  | 3.9  | 3         |
| 16 | Improved Schottky contacts to InGaIn alloys by a photoelectrochemical treatment. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016, 213, 1034-1038.   | 1.8  | 0         |